

FORM PTO-1449				Atty. Docket No. XA-10097		Appln. No. <b>28/501391</b>	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b>				Applicant Michitaro KANAMITSU et al.			
				Filing Date Herewith		Group <b>2827</b>	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
<i>AT</i>	AH	11-250681	9/17/99	Japan			No
<i>I</i>	AI	7-307098	11/21/95	Japan			No
<i>MT</i>	AJ	10-188576	7/21/98	Japan			No
	AK						
	AL						
	AM						
	AN						
<b>OTHER (including author, title, date, pertinent pages, etc.)</b>							
<i>MT</i>	AO	K. Imamiya et al., "MP6.6 A 130nm' 256 Mb NAND Flash with Shallow Trench Isolation Technology", <u>1999 IEEE International Solid-State Circuits Conference</u> .					
<i>I</i>	AP	K. Suh et al., "TA7.5: A 3.3V 32 Mb NAND Flash Memory with Incremental Step Pulse Programming Scheme", <u>1995 IEEE International Solid-State Circuits Conference</u> , pp. 128-129.					
<i>MT</i>	AQ	K. Imamiya et al., "TA7.6: A 35 ns-Cycle-Time 3.3V-Only 32 Mb NAND Flash EEPROM", <u>1995 IEEE International Solid-State Circuits Conference</u> , pp. 130-131.					
Examiner <i>M. TRAN</i>				Date Considered <b>3/19/05</b>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.							